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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	37
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10rjagfa-v0

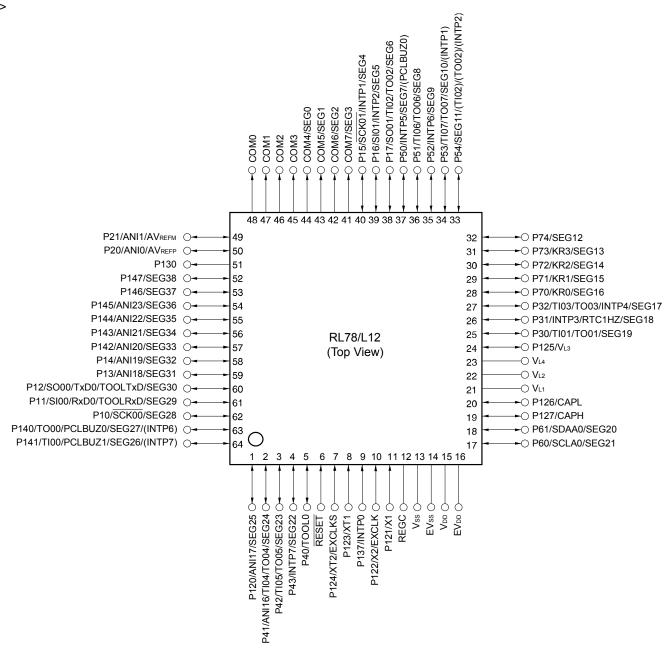
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RL78/L12 1. OUTLINE

- 64-pin plastic LQFP (fine pitch) (10 × 10)
- 64-pin plastic LQFP (12 × 12)

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- Cautions 1. Make EVss pin the same potential as Vss pin.
 - 2. Make VDD pin the same potential as EVDD pin.
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD} pins and connect the V_{SS} and EV_{SS} pins to separate ground lines.
 - **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

RL78/L12 OUTLINE

1.6 Outline of Functions

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H

(1/2)Item 32-pin 44-pin 48-pin 52-pin 64-pin R5F10RBx R5F10RFx R5F10RGx R5F10RJx R5F10RLx Code flash memory (KB) 8 to 32 8 to 32 8 to 32 8 to 32 16, 32 2 Data flash memory (KB) 2 2 2 2 1, 1.5 Note 1 1, 1.5 Note 1 1, 1.5 Note 1 1, 1.5^{Note 1} 1. 1.5 Note 1 RAM (KB) 1 MB Memory space X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) Main High-speed system clock system HS (high-speed main) operation: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), clock HS (high-speed main) operation: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) operation: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) operation: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V) High-speed on-chip HS (high-speed main) operation: 1 to 24 MHz (V_{DD} = 2.7 to 5.5 V), oscillator clock HS (high-speed main) operation: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) operation: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) operation: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V) Subsystem clock XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz (TYP.): VDD = 1.6 to 5.5 V Low-speed on-chip oscillator clock Internal oscillation 15 kHz (TYP.): $V_{DD} = 1.6 \text{ to } 5.5 \text{ V}$ 8 bits × 32 registers (8 bits × 8 registers × 4 banks) General-purpose register Minimum instruction execution time 0.04167 μ s (High-speed on-chip oscillator clock: fih = 24 MHz operation) $0.05 \,\mu s$ (High-speed system clock: f_{MX} = 20 MHz operation) 30.5 μ s (Subsystem clock: f_{SUB} = 32.768 kHz operation) Instruction set • Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. Total number of I/O port pins and 40 44 58 28 48 pins dedicated to drive an LCD I/O Total 20 33 37 47 29 port CMOS I/O 15 22 26 30 39 CMOS input 3 5 5 5 5 CMOS output 1 N-ch open-drain I/O 2 2 2 2 2 (EV_{DD} tolerance) Pins dedicated to drive an LCD 8 11 11 LCD controller/driver Internal voltage boosting method, capacitor split method, and external resistance division method are switchable. 26 (22) Note 2 39 (35) Note 2 22 (18) Note 2 30 (26) Note 2 13 Segment signal output 4 (8) Note 2

Notes 1. In the case of the 1 KB, and 1.5 KB, this is 630 bytes when the self-programming function and data flash function is used.

2. The values in parentheses are the number of signal outputs when 8 com is used.



4

Common signal output

RL78/L12 1. OUTLINE

(2/2)

1		1	1			(2/2
	Item	32-pin	44-pin	48-pin	52-pin	64-pin
		R5F10RBx	R5F10RFx	R5F10RGx	R5F10RJx	R5F10RLx
Timer	16-bit timer	8 channels	8 channels	(with 1 channel i	emote control ou	tput function)
	Watchdog timer			1 channel		
	Real-time clock (RTC)			1 channel		
	12-bit interval timer (IT)			1 channel		
	Timer output	4 channels (PWM outputs: 3 Note 1)	5 channels (PWM outputs: 4 Note 1)	6 channels (PWM outputs: 5 Note 1)	8 channels (PWN	1 outputs: 7 ^{Note 1})
	RTC output	-	1 • 1 Hz (subsyst	tem clock: fsuв =	32.768 kHz or)	
Clock output/b	ouzzer output	1			2	
		(Main system • 256 Hz, 512 32.768 kHz	n clock: f _{MAIN} = 20	MHz operation) .048 kHz, 4.096	kHz, 8.192 kHz, 1	
8/10-bit resolu	ution A/D converter	4 channels	7 channels	9 channels	10 channels	10 channels
Serial interfac	e	CSI: 2 chann	el/UART (LIN-bu	s supported): 1 o	channel	
I ² C bus		1 channel	1 channel	1 channel	1 channel	1 channel
Multiplier and accumulator	divider/multiply-	• 32 bits ÷ 32 bits	its = 32 bits (Uns its = 32 bits (Uns its + 32 bits = 32	igned)		
DMA controlle	er	2 channels				
Vectored inter	rupt Internal	23	23	23	23	23
sources	External	4	6	7	7	9
Key interrupt	•			4	ı	
Reset		Internal resetInternal resetInternal resetInternal reset	SET pin by watchdog tim by power-on-res by voltage detec by illegal instruc by RAM parity e by illegal-memor	et ctor tion execution ^{No} rror	ote 2	
Power-on-reset circuit • Power-on-reset: 1.51 ±0.04 V • Power-down-reset: 1.50 ±0.04 V						
Voltage detec	tor		1.67 V to 4.06 V 1.63 V to 3.98 V			
On-chip debu	g function	Provided				
Power supply	voltage	V _{DD} = 1.6 to 5.5	V			
Operating am	bient temperature	T _A = -40 to +85	o °C			

Notes 1. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves).

2. The illegal instruction is generated when instruction code FFH is executed. Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C)

(1/3)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}	V _{DD} = EV _{DD}	-0.5 to +6.5	V
	EV _{DD}	V _{DD} = EV _{DD}	-0.5 to +6.5	V
	EVss		-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} + 0.3 ^{Note 1}	V
Input voltage	V _{I1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	-0.3 to EV _{DD} +0.3 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
	V ₁₂	P60, P61 (N-ch open-drain)	-0.3 to EV _{DD} +0.3 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
	Vıз	P20, P21, P121 to P124, P137, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} + 0.3 ^{Note 2}	V
Output voltage	Vo1	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P60, P61, P70 to P74, P120, P125 to P127, P130, P140 to P147	-0.3 to EV _{DD} + $0.3and -0.3 to VDD + 0.3Note 2$	V
	V _{O2}	P20, P21	-0.3 to V _{DD} + 0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI23	-0.3 to EV _{DD} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 Notes 2, 3	٧
	VAI2	ANIO, ANI1	-0.3 to V _{DD} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 Notes 2,3	٧

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed $AV_{REF(+)} + 0.3 V$ in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** AV_{REF(+)}: + side reference voltage of the A/D converter.
 - 3. Vss: Reference voltage

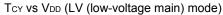
(Ta = -40 to +85°C, 1.6 V \leq EV_{DD} = V_{DD} \leq 5.5 V, Vss = EVss = 0 V)

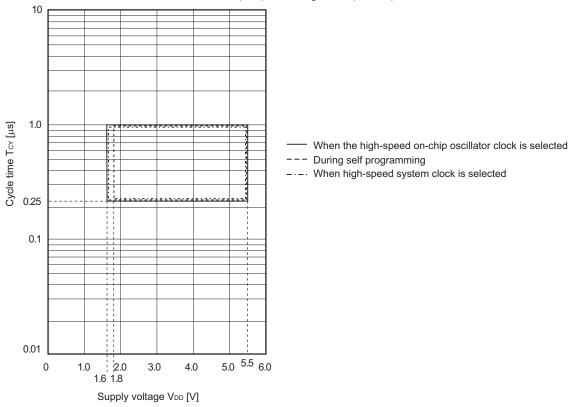
(3/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	Normal input buffer	0.8EV _{DD}		EV _{DD}	٧
	V _{IH2}	P10, P11, P15, P16	TTL input buffer 4.0 V ≤ EV _{DD} ≤ 5.5 V	2.2		EV _{DD}	V
			TTL input buffer 3.3 V ≤ EV _{DD} < 4.0 V	2.0		EV _{DD}	V
			TTL input buffer 1.6 V ≤ EV _{DD} < 3.3 V	1.50		EV _{DD}	V
	V _{IH3}	P20, P21		0.7V _{DD}		V _{DD}	V
	V _{IH4}	P60, P61		0.7EV _{DD}		EV _{DD}	V
	V _{IH5}	P121 to P124, P137, EXCLK, EXCLK	S, RESET	0.8V _{DD}		V _{DD}	V
Input voltage, low	VIL1	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	Normal input buffer	0		0.2EV _{DD}	V
	V _{IL2}	P10, P11, P15, P16	TTL input buffer 4.0 V ≤ EV _{DD} ≤ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V ≤ EV _{DD} < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EV _{DD} < 3.3 V	0		0.32	V
	V _{IL3}	P20, P21		0		0.3V _{DD}	V
	V _{IL4}	P60, P61		0		0.3EV _{DD}	V
	V _{IL5}	P121 to P124, P137, EXCLK, EXCLK	S, RESET	0		0.2V _{DD}	٧

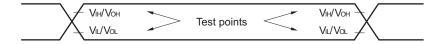
Caution The maximum value of VIH of P10, P12, P15, P17 is EVDD, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

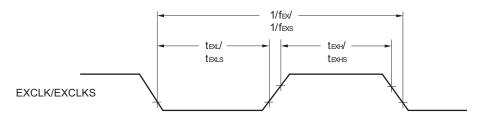




AC Timing Test Points



External System Clock Timing



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS} = 0 \text{ V})$

Parameter	Symbol	(Conditions	, ,	h-speed Mode	,	/-speed Mode	,	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	2.7 V ≤ EV	/ _{DD} ≤ 5.5 V	167 Note 1		500 Note 1		1000 Note 1		ns
		2.4 V ≤ EV	/ _{DD} ≤ 5.5 V	250 Note 1		500 Note 1		1000 Note 1		ns
		1.8 V ≤ EV	/ _{DD} ≤ 5.5 V			500 Note 1		1000 Note 1		ns
		1.6 V ≤ EV	/ _{DD} ≤ 5.5 V					1000 Note 1		ns
SCKp high-/low-level width	tкн1, tкL1	4.0 V ≤ EV	/ _{DD} ≤ 5.5 V	tксү1/2 - 12		tkcy1/2 - 50		tксү1/2 - 50		ns
		2.7 V ≤ EV	/ _{DD} ≤ 5.5 V	tксү1/2 - 18		tkcy1/2 - 50		tксү1/2 - 50		ns
		2.4 V ≤ E\	/ _{DD} ≤ 5.5 V	tkcy1/2 - 38		tксү1/2 - 50		tkcy1/2 - 50		ns
		1.8 V ≤ E\	/ _{DD} ≤ 5.5 V			tксү1/2 - 50		tксү1/2 - 50		ns
		1.6 V ≤ E\	/ _{DD} ≤ 5.5 V					tkcy1/2 - 100		ns
SIp setup time (to SCKp↑)	t sıĸı	2.7 V ≤ EV	/ _{DD} ≤ 5.5 V	44		110		110		ns
Note 2		2.4 V ≤ EV	/ _{DD} ≤ 5.5 V	75		110		110		ns
		1.8 V ≤ EV	/ _{DD} ≤ 5.5 V			110		110		ns
		1.6 V ≤ EV	/ _{DD} ≤ 5.5 V					220		ns
SIp hold time (from SCKp [↑])	t KSI1	2.4 V ≤ EV	/ _{DD} ≤ 5.5 V	19		19		19		ns
•		1.8 V ≤ E\	/ _{DD} ≤ 5.5 V			19		19		
		1.6 V ≤ EV	/ _{DD} ≤ 5.5 V					19		
Delay time from SCKp↓ to	t KSO1	C = 30 pF	2.4 V ≤ EV _{DD} ≤ 5.5 V		25		25		25	ns
SOp output Note 4		14016 3	1.8 V ≤ EV _{DD} ≤ 5.5 V				25		25	
			$1.6 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$						25	

Notes 1. For CSI00, set a cycle of 2/fmck or longer. For CSI01, set a cycle of 4/fmck or longer.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp \downarrow " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 5. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

(Remarks are listed on the next page.)

Remarks 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 1)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).

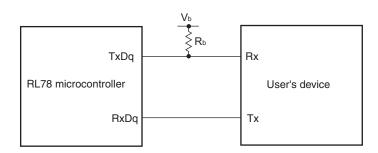
m: Unit number, n: Channel number (mn = 00, 01))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2) (T_A = −40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

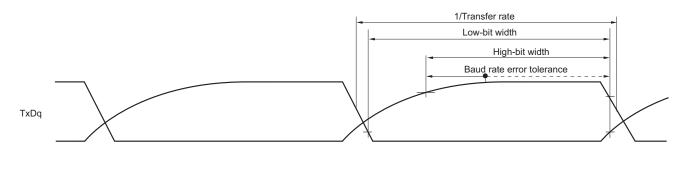
Parameter	Symbol	Cond	itions	HS (high		LS (low main)			-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time ^{Note}	tkcy2	$4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}$	20 MHz < fмск	8/ƒмск						ns
5			fмck ≤ 20 MHz	6/ƒмск		6/fмск		6/fмск		ns
		2.7 V ≤ EV _{DD} < 4.0 V	16 MHz < f _{MCK}	8/fмск						ns
			f _{MCK} ≤ 16 MHz	6/ƒмск		6/fмск		6/fмск		ns
		$2.4 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$		6/fмск and 500		6/ƒмск		6/ƒмск		ns
		1.8 V ≤ EV _{DD} < 2.4 V				6/fмск		6/ƒмск		ns
		1.6 V ≤ EV _{DD} < 1.8 V						6/ƒмск		ns
SCKp high-/low- level width	tkH2, tkL2	$4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		tксү2/2 - 7		tксү2/2 -7		tксү2/2 -7		ns
		2.7 V ≤ EV _{DD} < 4.0 V		tксү2/2 - 8		tkcy2/2 -8		tксү2/2 -8		ns
		2.4 V ≤ EV _{DD} < 2.7 V		tксү2/2 - 18		t _{KCY2} /2 - 18		t _{KCY2} /2 - 18		ns
		1.8 V ≤ EV _{DD} < 2.4 V				tkcy2/2 - 18		tксү2/2 - 18		ns
		1.6 V ≤ EV _{DD} < 1.8 V						tkcy2/2 -66		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsık2	$2.7~\text{V} \leq \text{EV}_{\text{DD}} \leq 5.5~\text{V}$		1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		2.4 V ≤ EV _{DD} < 2.7 V		1/fмск + 30		1/fмск + 30		1/fмск + 30		
		1.8 V ≤ EV _{DD} < 2.4 V				1/fмск + 30		1/fмск + 30		ns
		1.6 V ≤ EV _{DD} < 1.8 V						1/fмск + 40		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi2	$2.4~\text{V} \leq \text{EV}_{\text{DD}} \leq 5.5~\text{V}$		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
		1.8 V ≤ EV _{DD} < 2.4 V				1/fмск + 31		1/fмск + 31		ns
		1.6 V ≤ EV _{DD} < 1.8 V						1/fмск + 250		ns

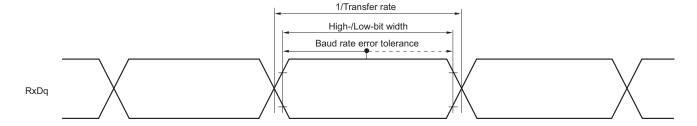
(Notes, Caution, and Remarks are listed on the next page.)

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remarks 1.** $R_b[\Omega]$:Communication line (TxDq) pull-up resistance, $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 - 2. q: UART number (q = 0, 1), g: PIM and POM number (g = 1)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3) (T_A = −40 to +85°C, 1.8 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	speed	high- I main) ode	speed	(low- main) ode	voltage	(low- e main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tsıĸ1	$ \begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array} $	81		479		479		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \ R_{\text{b}} = 2.7 \text{ k}\Omega $	177		479		479		ns
		$ 2.4 \text{ V} \leq \text{EV}_{\text{DD}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \ R_{\text{b}} = 5.5 \text{ k}\Omega $	479		479		479		ns
		$\begin{array}{l} 1.8 \ V \leq EV_{DD} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 3}}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$			479		479		ns
SIp hold time (from SCKp↑) Note 1	t _{KSI1}	$ \begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array} $	19		19		19		ns
		$ \begin{array}{l} 2.7 \; \text{V} \leq \text{EV}_{\text{DD}} < 4.0 \; \text{V}, 2.3 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.7 \; \text{V}, \\ \text{C}_{\text{b}} = 30 \; \text{pF}, \; \text{R}_{\text{b}} = 2.7 \; \text{k}\Omega \end{array} $	19		19		19		ns
		$ 2.4 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}, \\ C_b = 30 \text{ pF}, \ R_b = 5.5 \text{ k}\Omega $	19		19		19		ns
		1.8 $V \le EV_{DD} < 3.3 V$, 1.6 $V \le V_b \le 2.0 V^{Note 3}$, $C_b = 30 pF$, $R_b = 5.5 kΩ$			19		19		ns
Delay time from SCKp↓ to SOp output Note 1	tkso1	$ \begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array} $		100		100		100	ns
		$ 2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}, \\ C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega $		195		195		195	ns
		$ \begin{array}{l} 2.4 \; V \leq EV_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array} $		483		483		483	ns
		1.8 V \leq EV _{DD} < 3.3 V, 1.6 V \leq V _b \leq 2.0 V ^{Note 3} , C _b = 30 pF, R _b = 5.5 kΩ				483		483	ns
SIp setup time (to SCKp↓) Note 2	tsıĸ1	$ \begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array} $	44		110		110		ns
		$ 2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}, \\ C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega $	44		110		110		ns
		$ 2.4 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \ R_{\text{b}} = 2.7 \text{ k}\Omega $	110		110		110		ns
		$\begin{array}{l} 1.8 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V}^{\text{Note 3}}, \\ C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega \end{array}$			110		110		ns

Notes

- 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. Use it with $EV_{DD} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (32-pin to 52-pin products)/EVDD tolerance (64-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input) $(T_A = -40 \text{ to } +85^{\circ}\text{C}. 1.8 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS} = 0 \text{ V})$ (1/2)

(1A = -40 to +65	°C, 1.8 V	$V \le EV_{DD} = V_{DD} \le 5.5 \text{ V}, \text{ Vss} = EV_{SS} = 0 \text{ V}$							(1/2)	
Parameter	Symbol	Conditions			high- main) ode	'	/-speed mode	mo	e main) ode	Unit
			_	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V},$	20 MHz < fмck ≤ 24 MHz	12/f мск						ns
		$2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$	8 MHz < fмck ≤ 20 MHz	10/f мск						ns
			4 MHz < fMck ≤ 8 MHz	8/fмск		16/f мск				ns
			fмck ≤ 4 MHz	6/fмск		10/fмск		10/f мск		ns
		$2.7 \text{ V} \le \text{EV}_{DD} \le 4.0 \text{ V},$	20 MHz < f _{MCK} ≤ 24 MHz	16/f мск						ns
		$2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}$	16 MHz < fмck ≤ 20 MHz	14/f мск						ns
			8 MHz < f _{MCK} ≤ 16 MHz	12/f мск						ns
			4 MHz < f _{MCK} ≤ 8 MHz	8/fмск		16/fмск				ns
			fмck ≤4 MHz	6/fмск		10/fмск		10/fмск		ns
		2.4 V ≤ EV _{DD} < 3.3 V,	20 MHz < f _{MCK} ≤ 24 MHz	36/fмск						ns
		$1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}$	16 MHz < f _{MCK} ≤ 20 MHz	32/fмск						ns
			8 MHz < fмcк ≤ 16 MHz	26/fмск						ns
			4 MHz < fMCK ≤ 8 MHz	16/f мск		16/fмск				ns
			fмck≤4 MHz	10/fмск		10/fмск		10/fмск		ns
		1.8 V ≤ EV _{DD} < 3.3 V,	4 MHz < f _{MCK} ≤ 8 MHz			16/fмск				ns
		$1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}^{\text{Note 2}}$	fмcк≤4 MHz			10/fмск		10/f мск		ns
SCKp high-/low-level width	t _{KH2} ,	4.0 V ≤ EV _{DD} ≤ 5.5 V	$V_{\rm t}, 2.7 \ {\rm V} \le {\rm V_b} \le 4.0 \ {\rm V}$	tkcy2/2 - 12		txcy2/2 - 50		tkcy2/2 - 50		ns
		2.7 V ≤ EV _{DD} < 4.0 V	$V_{1}, 2.3 \text{ V} \le V_{b} \le 2.7 \text{ V}$	tkcy2/2 - 18		txcy2/2 - 50		tkcy2/2 - 50		ns
		2.4 V ≤ EV _{DD} < 3.3 V	$V_{1}, 1.6 \text{ V} \le V_{b} \le 2.0 \text{ V}$	tkcy2/2 - 50		txcy2/2 - 50		tkcy2/2 - 50		ns
		$1.8 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V}$ $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}^{\text{Not}}$				tkcy2/2 - 50		tkcy2/2 - 50		ns
SIp setup time (to SCKp↑) Note 3	tsik2	4.0 V ≤ EV _{DD} < 5.5 V	$V_{b} \leq V_{b} \leq 4.0 \text{ V}$	1/f _{MCK} + 20		1/f _{MCK} + 30		1/fmck + 30		ns
		2.7 V ≤ EV _{DD} < 4.0 V	$V_{c}, 2.3 \text{ V} \le V_{b} \le 2.7 \text{ V}$	1/f _{MCK} + 20		1/fmck + 30		1/fmck + 30		ns
		2.4 V ≤ EV _{DD} < 3.3 V	V_{b} , 1.6 $V \le V_{b} \le 2.0 V$	1/f _{MCK} + 30		1/fmck + 30		1/fmck + 30		ns
		$1.8 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V}$ $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}^{\text{Not}}$				1/fmck + 30		1/fmck + 30		ns
SIp hold time (from SCKp↑) Note 4	tksi2	4.0 V ≤ EV _{DD} < 5.5 V	$V_{1}, 2.7 \text{ V} \le V_{b} \le 4.0 \text{ V}$	1/f _{MCK} + 31		1/fmck+ 31		1/f _{MCK} + 31		ns
		2.7 V ≤ EV _{DD} < 4.0 V	$V_{1}, 2.3 \text{ V} \le V_{b} \le 2.7 \text{ V}$	1/f _{MCK} + 31		1/f _{MCK} + 31		1/f _{MCK} + 31		ns
		2.4 V ≤ EV _{DD} < 3.3 V	$V_{1}, 1.6 \text{ V} \le V_{b} \le 2.0 \text{ V}$	1/f _{MCK} + 31		1/fmck+ 31		1/f _{MCK} + 31		ns
		$1.8 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V}$ $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}^{\text{Not}}$				1/f _{MCK} + 31		1/f _{MCK} + 31		ns

(Notes, Caution and Remarks are listed on the next page.)

(3) I²C fast mode plus

(TA = -40 to +85°C, 1.6 V \leq EVDD = VDD \leq 5.5 V, Vss = EVss = 0 V)

Parameter	Symbol	Conditions		h-speed Mode	LS (low main)		`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode plus: $f_{CLK} \ge 10 \text{ MHz}$ $2.7 \text{ V} \le EV_{DD} \le 5.5 \text{ V}$	0	1000	_	-	_	_	kHz
Setup time of restart condition	tsu:sta	2.7 V ≤ EV _{DD} ≤ 5.5 V	0.26		_	_	_	_	μs
Hold time ^{Note 1}	thd:STA	2.7 V ≤ EV _{DD} ≤ 5.5 V	0.26		_	-	_	-	μS
Hold time when SCLA0 = "L"	t _{LOW}	2.7 V ≤ EV _{DD} ≤ 5.5 V	0.5			-		-	μs
Hold time when SCLA0 = "H"	t HIGH	$2.7 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$	0.26		_	-	_	-	μs
Data setup time (reception)	tsu:dat	2.7 V ≤ EV _{DD} ≤ 5.5 V	50		_	-	_	_	μs
Data hold time (transmission) ^{Note 2}	thd:dat	2.7 V ≤ EV _{DD} ≤ 5.5 V	0	0.45	_	-	_	_	μs
Setup time of stop condition	t su:sто	2.7 V ≤ EV _{DD} ≤ 5.5 V	0.26		_	-	_	_	μs
Bus-free time	t BUF	2.7 V ≤ EV _{DD} ≤ 5.5 V	0.5			-	_	_	μS

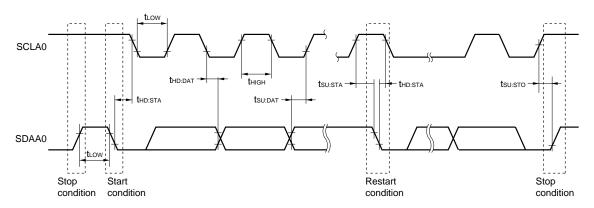
- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: $C_b = 120 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS} = 0 \text{ V})$

(1/5)

Items	Symbol		Conditions	MIN.	TYP.	MAX.	Unit	
Output current, high ^{Note 1}	Іон1		Per pin for P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P130, P140 to P147				-3.0 Note 2	mA
		Total of P10 to P14, F	P40 to P43, P120,	$4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$			-30.0	mA
		P130, P140 to P147 (When duty = 70% Not	e 3、	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 4.0 \text{ V}$			-8.0	mA
		(vvnen duty = 70%)	$2.4 \text{ V} \leq \text{EV}_{DD} \leq 2.7 \text{ V}$			-4.0	mA
		Total of P15 to P17, F	P30 to P32,	$4.0~V \leq EV_{DD} \leq 5.5~V$			-30.0	mA
		P50 to P54, P70 to P7	,	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 4.0 \text{ V}$			-15.0	mA
		(When duty = 70% Not)	$2.4 \text{ V} \leq \text{EV}_{DD} \leq 2.7 \text{ V}$			-8.0	mA
		Total of all pins (When duty = 70% Note	*3)				-60.0	mA
	І он2	P20, P21	Per pin			-0.1	mA	
			Total of all pins	$2.4~V \leq V_{DD} \leq 5.5~V$			-0.2	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} and EV_{DD} pins to an output pin.
 - 2. Do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoH × 0.7)/(n × 0.01)
- <Example> Where n = 80% and IOH = -30.0 mA

Total output current of pins = $(-30.0 \times 0.7)/(80 \times 0.01) \approx -26.25$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P10, P12, P15, and P17 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into V_{DD} and EV_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD} or V_{SS}, EV_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, watchdog timer, and LCD controller/driver.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{Q}1 \text{ MHz}$ to 24 MHz $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{Q}1 \text{ MHz}$ to 16 MHz
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

3.4 AC Characteristics

3.4.1 Basic operation

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS} = 0 \text{ V})$

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Tcy	Main	HS (high-speed	$2.7 V \le V_{DD} \le 5.5 V$	0.04167		1	μS
instruction execution time)		system clock (f _{MAIN}) operation	main) mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		Subsystem of operation	lock (fsuв)	2.4 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self	HS (high-speed	$2.7 \text{V} \le \text{V}_{DD} \le 5.5 \text{V}$	0.04167		1	μS
		programming mode	main) mode	$2.4 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}$	0.0625		1	μS
External system clock frequency	fex	2.7 V ≤ V _{DD} ≤	5.5 V		1.0		20.0	MHz
		2.4 V ≤ V _{DD} <	2.7 V		1.0		16.0	MHz
	fexs				32		35	kHz
External system clock input high-	texh, texl	2.7 V ≤ V _{DD} ≤	≤ 5.5 V		24			ns
level width, low-level width		2.4 V ≤ V _{DD} <	2.7 V		30			ns
	texhs, texhs				13.7			μs
TI00 to TI07 input high-level width, low-level width	tтıн, tтı∟				1/fмск+10			ns
TO00 to TO07 output frequency	fто	HS (high-spe	ed 4.0 V	≤ EV _{DD} ≤ 5.5 V			16	MHz
		main) mode	2.7 V	≤ EV _{DD} < 4.0 V			8	MHz
			2.4 V	≤ EV _{DD} < 2.7 V			4	MHz
PCLBUZ0, PCLBUZ1 output	f PCL	HS (high-spe	ed 4.0 V	≤ EV _{DD} ≤ 5.5 V			16	MHz
frequency		main) mode	2.7 V	≤ EV _{DD} < 4.0 V			8	MHz
			2.4 V	≤ EV _{DD} < 2.7 V			4	MHz
Interrupt input high-level width,	tinth,	INTP0	2.4 V	≤ V _{DD} ≤ 5.5 V	1			μs
low-level width	t intl	INTP1 to INT	P7 2.4 V :	≤ EV _{DD} ≤ 5.5 V	1			μs
Key interrupt input low-level width	t kr	KR0 to KR3	2.4 V	≤ EV _{DD} ≤ 5.5 V	250			ns
RESET low-level width	trsL		•		10			μS

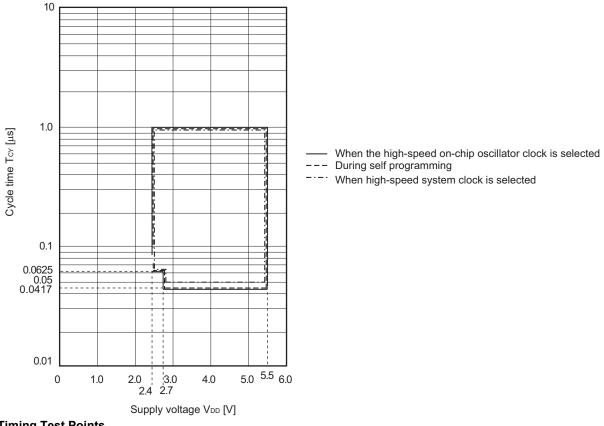
Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n).

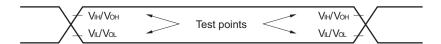
n: Channel number (n = 0 to 7))

Minimum Instruction Execution Time during Main System Clock Operation

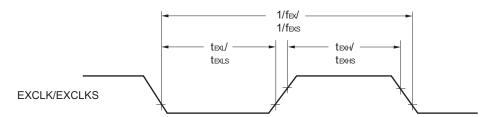
Tcy vs VDD (HS (high-speed main) mode)



AC Timing Test Points



External System Clock Timing



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS} = 0 \text{ V})$

Parameter	Symbol	Cond	litions	HS (high-spee	ed main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		334 Note 1		ns
		2.4 V ≤ EV _{DD} ≤ 5.5 V		500 Note 1		ns
SCKp high-/low-level width	t кн1,	4.0 V ≤ EV _{DD} ≤ 5.5 V		tkcy1/2 - 24		ns
	t KL1	$2.7~V \leq EV_{DD} \leq 5.5~V$		tkcy1/2 - 36		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		tkcy1/2 - 76		ns
SIp setup time (to SCKp↑) Note 2	tsik1	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		66		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		113		ns
SIp hold time (from SCKp↑) Note 3	t _{KSI1}	$2.4 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		38		ns
Delay time from SCKp↓ to SOp output Note 4	tkso1	C = 30 pF Note 5	$2.4~V \le EV_{DD} \le 5.5~V$		50	ns

Notes 1. Set a cycle of 4/fmck or longer.

- **2.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp \downarrow " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 5. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 1)
 - 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(4) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \leq \text{EV}_{DD} = \text{V}_{DD} \leq 5.5 \text{ V}, \text{Vss} = \text{EVss} = 0 \text{ V})$

Parameter	Symbol	Conditions			HS (high-spee	Unit	
					MIN.	MAX.	
Transfer rate	Reception	Reception	$ 4.0 \ V \le EV_{DD} \le 5.5 \ V, $ $ 2.7 \ V \le V_b \le 4.0 \ V $			fmck/12 Note 1	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 2		2.0	Mbps
			$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$			fмск/12 Note 1	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 2		2.0	Mbps
		$2.4 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}$			fMCK/12 Note 1	bps	
				Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} Note 2		2.0	Mbps

- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
 - 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (32- to 52-pin products)/EV_{DD} tolerance (64-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

- Remarks 1. V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0), g: PIM and POM number (g = 1)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01)

(4) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS} = 0 \text{ V})$

(2/2)

	Transmission	4.0 V ≤ EV _{DD} ≤ 5.5 V,		MIN.	MAX.	
	Transmission	40V <fvpp<55v< td=""><td></td><td></td><td></td><td></td></fvpp<55v<>				
					Note 1	bps
		$2.7 \text{ V} \le V_b \le 4.0 \text{ V}$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.0 Note 2	Mbps
		2.7 V ≤ EV _{DD} < 4.0 V,			Note 3	bps
		$2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate		1.2 Note 4	Mbps
	2.4 V ≤ EV _{DD} < 3.3 V,			Note 5	bps	
		$1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate		0.43 Note 6	Mbps
			2.4 V ≤ EV _{DD} < 3.3 V,	$maximum \ transfer \ rate$ $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega, \ V_b = 2.3 \ V$ $2.4 \ V \le EV_{DD} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V$ Theoretical value of the maximum transfer rate	$maximum \ transfer \ rate$ $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega, \ V_b = 2.3 \ V$ $2.4 \ V \le EV_{DD} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V$ Theoretical value of the	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

$$\label{eq:maximum transfer rate} \begin{aligned} & \frac{1}{\{-C_b \times R_b \times \text{ln } (1-\frac{2.2}{V_b})\} \times 3} \text{ [bps]} \end{aligned}$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **2.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DD} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \text{ln } (1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

3.6.4 LVD circuit characteristics

(Ta = -40 to +105°C, $V_{PDR} \le EV_{DD} = V_{DD} \le 5.5 \text{ V}$, $V_{SS} = EV_{SS} = 0 \text{ V}$)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Detection Supply voltage level		Power supply rise time	3.90	4.06	4.22	V
voltage			Power supply fall time	3.83	3.98	4.13	٧
		V _{LVD1}	Power supply rise time	3.60	3.75	3.90	V
			Power supply fall time	3.53	3.67	3.81	٧
		V _{LVD2}	Power supply rise time	3.01	3.13	3.25	V
			Power supply fall time	2.94	3.06	3.18	٧
		V _{LVD3}	Power supply rise time	2.90	3.02	3.14	V
			Power supply fall time	2.85	2.96	3.07	V
		V _{LVD4}	Power supply rise time	2.81	2.92	3.03	V
			Power supply fall time	2.75	2.86	2.97	V
		V _{LVD5}	Power supply rise time	2.70	2.81	2.92	V
			Power supply fall time	2.64	2.75	2.86	V
		V _{LVD6}	Power supply rise time	2.61	2.71	2.81	V
			Power supply fall time	2.55	2.65	2.75	V
		V _{LVD7}	Power supply rise time	2.51	2.61	2.71	V
			Power supply fall time	2.45	2.55	2.65	V
Minimum pu	Minimum pulse width			300			μs
Detection de	elay time					300	μs

LVD Detection Voltage of Interrupt & Reset Mode

(Ta = -40 to +105°C, $V_{PDR} \le EV_{DD} = V_{DD} \le 5.5 \text{ V}$, $V_{SS} = EV_{SS} = 0 \text{ V}$)

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	V _{LVDD0}	VPOC2, VPOC1, VPOC	:0 = 0, 1, 1, 1	falling reset voltage	2.64	2.75	2.86	٧
mode	VLVDD1	LVIS1, LVI	IS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
				Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2	LVIS1, LVI	IS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	٧
	V _{LVDD3}	LVIS1, LVI	ISO = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
				Falling interrupt voltage	3.83	3.98	4.13	٧

3.6.5 Power supply voltage rising slope characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 31.4 AC Characteristics.